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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 1 of 3

Complete if Known	
Application Number	10/774,515
Filing Date	February 10, 2004
First Named Inventor	John T. Moore, et al.
Art Unit	~~2815~~ 2813
Examiner Name	Not Yet Assigned
Attorney Docket Number	M4065.0697//P697-A

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Examiner Initials*	Cite No.[1]	Document Number Number-Kind Code[2] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	A	US 2004/0035401	2/2004	Ramachandran et al.	
	B	US 2003/0212724	11/2003	Ovshinsky et al.	
	C	US 2003/0048744	3/2003	Ovshinsky et al.	
	D	US 2003/0212725	11/2003	Ovshinsky et al.	
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	F	US 3,271,591	9/1966	Ovshinsky	
	G	US 3,961,314	6/1976	Klose et al.	
	H	US 3,966,317	6/1976	Wacks et al.	
	I	US 3,983,542	11/1976	Ovshinsky	
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	M	US 4,597,162	7/1986	Johnson et al.	
	N	US 4,608,296	8/1986	Keem et al.	
	O	US 4,637,895	1/1987	Ovshinsky et al.	
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	X	US 4,710,899	12/1987	Young et al.	
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	M2	US 6,437,383	8/2002	Xu	
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	X2	US 6,534,781	3/2003	Dennison	
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Art Unit	~~2815~~ 2813
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	S3	US 6,649,928	11/2003	Dennison		
	T3	US 6,667,900	12/2003	Lowery et al.		
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	B4	US 6,687,153	2/2004	Lowery		
	C4	US 6,707,712	3/2004	Lowery		
	D4	US 6,714,954	3/2004	Ovshinsky et al.		

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Examiner Initials*	Cite No.[1]	Foreign Patent Document: Country Code[3]-Number[4]-Kind Code[5] *(if known)*	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T[6]

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NON PATENT LITERATURE DOCUMENTS

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Jennifer M Dolan 12/8/04

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Sheet 1 of 8

Complete if Known	
Application Number	Not Yet Assigned 10/774515
Filing Date	February 10, 2004
First Named Inventor	John T. Moore
Art Unit	~~Not Yet Assigned~~ 2813
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Examiner Initials*	Cite No.[1]	Document Number Number-Kind Code[2] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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	AO	2003/0001229 APP	1/2/2003	Moore et al. **	
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	AW	2003/0035314	02/20/03	Kozicki **	
	AX	2003/0035315	02/20/03	Kozicki **	

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	BA	WO 97/48032	12/18/1997	Kozicki et al. **		
	BB	WO 99/28914	06/10/1999	Kozicki et al. **		
	BC					
	BD					

Examiner Signature		Date Considered	12/8/04

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OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
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	CB	Adler, D.; Moss, S.C., Amorphous memories and bistable switches, J. Vac. Sci. Technol. 9 (1972) 1182-1189. **	
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	CF	Alekperova, Sh.M.; Gadzhieva, G.S., Current-Voltage characteristics of Ag2Se single crystal near the phase transition, Inorganic Materials 23 (1987) 137-139. **	
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First Named Inventor	John T. Moore
Group Art Unit	Not Yet Assigned
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Form PTO-1449 — U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

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ATTY. DOCKET NO.	SERIAL NO.
MI22-1527	09/797,635
APPLICANT: John T. Moore et al.	
FILING DATE: March 1, 2001	GROUP: 2813

U.S. PATENT DOCUMENTS

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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

JMS	AR		Kluge, et al., "Silver photodiffusion in amorphous Ge_xSe_{1-x}", Journal of Non-Crystalline Solids 124 (1990) pps. 186-193. ✱ ✱
JMS	AS		Kolobov, A.V., "Photodoping of amorphous chalcogenides by metals", Advances in Physics, 1991, Vol. 40, No. 5, pps. 625-684. ✱ ✱
JMS	AT		Mitkova, et al. "Dual Chemical Role of Ag as an Additive in Chalcogenide Glasses", Physical Review Letters, Vo.. 83, No. 19, pps. 3848-3851. ✱ ✱

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	AR		Mitkova, "Insulating and Semiconducting Glasses", Editor: P. Boolchand, World Scientific, New Jersey, 2000, pps. 813-843. **
	AS		
	AB		
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		FILING DATE Filed Herewith	GROUP Unknown

U.S. PATENT DOCUMENTS

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
JMS	AA	09/732,966		Gilton (as Filed)			12/08/2000
	AB	5,238,862	08/24/93	Blalock et al.	437	52	
	AC	5,360,981	11/01/94	Owen et al.	257	4	
	AD	5,761,115	06/02/98	Kozicki et al.	365	182	
	AE	5,896,312	04/20/99	Kozicki et al.	365	153	
	AF	5,914,893	06/22/99	Kozicki et al.	365	107	
JMS	AG	6,084,796	07/04/00	Kozicki et al.	365	153	
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JMS	AR		Axon Technologies Corporation, TECHNOLOGY DESCRIPTION: *Programmable Metallization Cell (PMC).*
			(pre-July 7, 2000) pp. 1-6.
JMS	AS		Shimakawa et al., *Photoinduced effects and metastability in amorphous semiconductors and insulators.*
			44 ADVANCES IN PHYSICS No. 6, 475-588 (Taylor & Francis Ltd. 1995)
	AT		

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JMS	AA	09/921,518		Moore (as filed and as amended) **			08/01/2001
	AB	10/061,825		Gilton et al. (as filed) **			01/31/2002
	AC	4,405,710	09/20/83	Balasubramanyam et al. **	430	311	
	AD	4,419,421	12/06/83	Wichelhaus et al. **	429	191	
	AE	4,499,557	02/12/85	Holmberg et al. **	365	163	
	AF	5,315,131	05/24/94	Kishimoto et al. **	257	57	
	AG	5,350,484	09/27/94	Gardner et al. **	156	628	
	AH	5,512,328	04/30/96	Yoshimura et al. **	427	498	
	AI	5,512,773	04/30/96	Wolf et al. **	257	471	
	AJ	5,846,889	12/08/98	Harbison et al. **	501	40	
JMS	AK	6,117,720	09/12/00	Harshfield **	438	238	

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		Document Number	Date	Country	Class	Subclass	Translation Yes	Translation No
JMS	AL	00/48196 A1	17.08.00	WIPO (Kozicki et al.) **				
JMS	AM	02/21542 A1	14.03.02	WIPO (Kozicki et al.) **				
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	AA	6,143,604	11/07/00	Chiang et al.	438	253	
	AB	6,177,338 B1	01/23/01	Liaw et al.	438	629	
	AC	6,350,679 B1	02/26/02	McDaniel et al.	438	634	
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*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	AA	3,622,319	11/23/71	Sharp	96	27	
	AB	3,743,847	07/03/73	Boland	250	510	
	AC	4,269,935	05/26/81	Masters et al.	430	323	
	AD	4,312,938	01/26/82	Drexler et al.	430	496	
	AE	4,320,191	03/16/82	Yoshikawa et al.	430	296	
	AF	4,795,657	01/03/89	Formigoni et al.	427	96	
	AG	4,847,674	07/11/89	Sliwa et al.	357	67	
	AH	5,177,567	01/05/93	Klersy et al.	257	4	
	AI	5,219,788	06/15/93	Abernathey et al.	437	187	
	AJ	5,726,083	03/10/98	Takaishi	438	210	
	AK	5,751,012	05/12/98	Wolstenholme et al.	257	5	

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	AN		Das et al., *Theory of the characteristic curves of the silver chalcogenide glass inorganic photoresists*, 54 APPL. PHYS. LETT., No. 18, pp. 1745-1747 (May 1989).
	AO		Helbert et al., *Intralevel hybrid resist process with submicron capability*, SPIE Vol. 333 SUBMICRON LITHOGRAPHY pp. 24-29 (1982)
	AP		Hilt, DISSERTATION: *Materials Characterization of Silver Chalcogenide Programmable Metallization Cells*, Arizona State University, pp. title page-114 (UMI Company, May 1999).

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JMM	AA	5,789,277	08/04/98	Zahorik et al.	438	95	
	AB	5,841,150	11/24/98	Gonzalez et al.	257	3	
	AC	5,920,788	07/06/99	Reinberg	438	466	
	AD	5,998,066	12/07/99	Block et al.	430	5	
	AE	6,077,729	06/20/00	Harshfield	438	128	
	AF	6,236,059 B1	05/22/01	Wolstenholme et al.	257	3	
	AG	6,297,170 B1	10/02/01	Gabriel et al.	438	738	
	AH	6,300,684 B1	10/09/01	Gonzalez et al.	257	774	
	AI	6,316,784 B1	11/13/01	Zahorik et al.	257	3	
	AJ	6,329,606 B1	12/11/01	Freyman et al.	174	260	
JMM	AK	6,348,365	02/19/02	Moore et al.	438	130	

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JMM	AN		Holmquist et al., *Reaction and Diffusion in Silver-Arsenic Chalcogenide Glass Systems*,
			62 J. AMER. CERAMIC SOC., Nos. 3-4, pp. 183-188 (Mar.-Apr. 1979).
JMM	AO		Huggett et al., *Development of silver sensitized germanium selenide photoresist by reactive*
			sputter etching in SF_6, 42 APPL. PHYS. LETT., No. 7, pp. 592-594 (April 1983).
JMM	AP		Kawaguchi et al., *Mechanism of photosurface deposition*, 164-166 J. NON-CRYST. SOLIDS,
			pp. 1231-1234 (1993).

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	AA	6,376,284 B1	04/23/02	Gonzalez et al.	438	129	
	AB	6,391,688 B1	05/21/02	Gonzalez et al.	438	128	
	AC	6,414,376 B1	07/02/02	Thakur et al.	257	640	
	AD	6,418,049 B1	07/09/02	Kozicki et al.	365	174	
	AE	6,423,628 B1	07/23/02	Li et al.	438	622	
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	AN	McHardy et al., *The dissolution of metals in amorphous chalcogenides and the effects of electron and ultraviolet radiation*, 20 J. PHYS. C: SOLID STATE PHYS., pp. 4055-4075 (1987).
	AO	Miyatani, *Electrical Porperties of Ag_2Se*, 13 J. Phys. Soc. Japan, p. 317 (1958).
	AP	Mizusaki et al. *Kinetic Studies on the Selenization of Silver*, 47 BUL. CHEM. SOC. JAPAN,, No. 11 pp. 2851-2855 (November 1974).

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JMS	AA	10/077,867		Campbell et al. (as filed) **			02/20/2002
JMS	AB	10/232,757		Li, et al. **			08/29/2002
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JMS	AN		Owens et al., *Metal-Chalcogenide Photoresists for High Resolution Lithography and Sub-Micron Structures*, NANOSTRUCTURE PHYSICS AND FABRICATION, pp. 447-451 (Academic Press, 1989). **
JMS	AO		Safran et al., *TEM study of Ag_2Se developed by the reaction of polycrystalline silver films and selenium*, 317 THIN SOLID FILMS, pp. 72-76 (1998). **
JMS	AP		Shimizu et al., *The Photo-Erasable Memory Switching Effect of Ag Photo-Doped Chalcogenide Glasses*, 46 BUL. CHEM. SOC. JAPAN, No. 12, pp. 3662-3665 (December 1973). **

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JMM	AN		Somogyi et al., *Temperature Dependence of the Carrier Mobility in Ag_2Se Layers Grown on*
			NaCl and SiO_2 Substrates, 74 ACTA PHYSICA HUNGARICA, No. 3, pp. 243-255 (1994). ✓✓
JMM	AO		Tai et al., *Multilevel Ge-Se film based resist systems*, SPIE Vol. 333 SUBMICRON LITHOGRAPHY,
			pp. 32-39 (March 1982). ✓✓
JMM	AP		Tai et al., *Submicron optical lithography using an inorganic resist/polymer bilevel scheme,*
			17 J. Vac. Sci. Technol., No. 5, pp. 1169-1176 (Sept./Oct. 1980). ✓✓

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	AN		West, DISSERTATION: *Electrically Erasable Non-Volatile Memory Via electrochemical Deposition of*
			Multifractal Aggregates, Arizona State University, pp. title page-168 (UMI Co., May 1998). ✓✓
	AO		West et al., *Equivalent Circuit Modeling of the Ag|$As_{0.24}S_{0.36}Ag_{0.40}$|Ag System Prepared by*
			Photodissolution of Ag, 145 J. Electrochem. Soc., No. 9, pp. 2971-2974 (September 1998). ✓✓
	AP		Yoshikawa et al., *A new inorganic electron resist of high contrast*, 31 APPL. PHYS. LETT., No. 3,
			pp. 161-163 (August 1977). ✓✓

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	AN		Yoshikawa et al., *Dry development of Se-Ge Inorganic photoresist*, 36 APPL. PHYS. LETT., No. 1,
			pp. 107-109 (January 1980). **
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